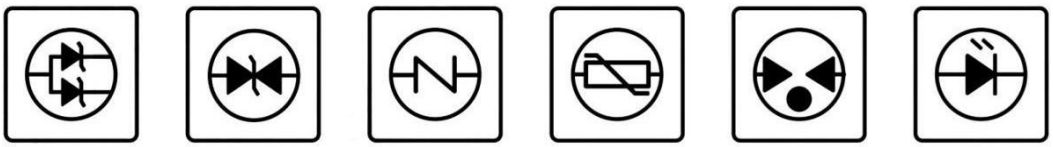
MSKSEMI 美森科
SEMICONDUCTOR



3N06-MS

Product specification

DESCRIPTION

The 3N06-MS uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltage as low as 2.5V.
This device is suitable for use as a battery protection or in other switching application.

3N06-MS N-Channel MOSFET

$V_{(BR)DSS}$	$R_{DS(on)}$MAX	I_D
60V	105mΩ@10V	3A
	125mΩ@4.5V	

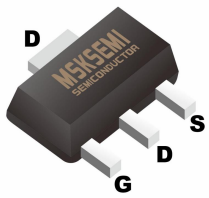
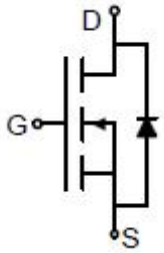
FEATURE

- High power and current handing capability
- Lead free product is acquired
- Surface mount package

APPLICATION

- Battery Switch
- DC/DC Converter

Reference News

PACKAGE OUTLINE	PIN CONFIGURATION	Marking
 SOT-89		MSKSEMI 3N06 MS

Maximum ratings (Ta=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current	I_D	3	A
Pulsed Drain Current (note 1)	I_{DM}	10	A
Power Dissipation	P_D	0.35	W
Thermal Resistance from Junction to Ambient (note 2)	$R_{\theta JA}$	357	℃/W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{STG}	-55~+150	℃

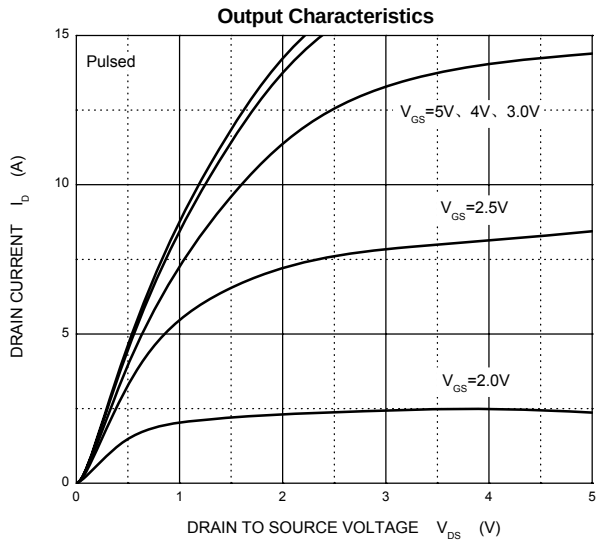
MOSFET ELECTRICAL CHARACTERISTICS Ta =25 ℃ unless otherwise specified

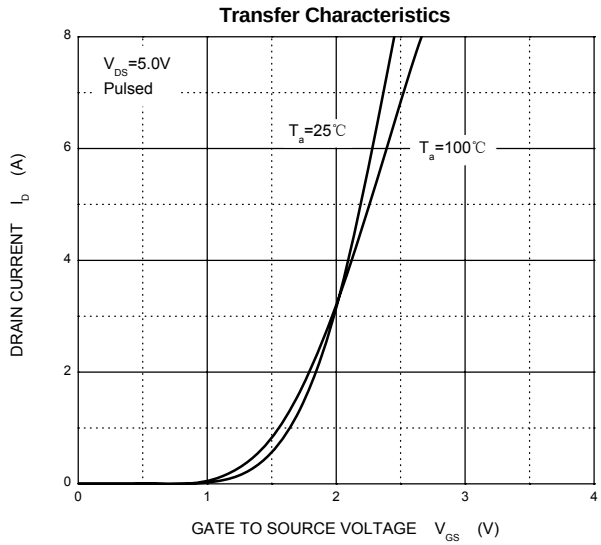
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
STATIC CHARACTERISTICS						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D =250μA	60			V
Zero gate voltage drain current	I_{DSS}	V_{DS} =60V,V_{GS} = 0V			1	μA
Gate-body leakage current	I_{GSS}	V_{GS} =±20V, V_{DS} = 0V			±100	nA
Gate threshold voltage (note 3)	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =250μA	0.5		2	V
Drain-source on-resistance (note 3)	$R_{DS(on)}$	V_{GS} =10V, I_D =3A			105	mΩ
		V_{GS} =4.5V, I_D =3A			125	mΩ
Forward tranconductance (note 3)	g_{FS}	V_{DS} =15V, I_D =2A	1.4			S
Diode forward voltage (note 3)	V_{SD}	I_S=3A, V_{GS} = 0V			1.2	V
DYNAMIC CHARACTERISTICS (note 4)						
Input Capacitance	C_{iss}	V_{DS} =30V,V_{GS} =0V,f =1MHz		247		pF
Output Capacitance	C_{oss}			34		pF
Reverse Transfer Capacitance	C_{rss}			19.5		pF
SWITCHING CHARACTERISTICS (note 4)						
Turn-on delay time	$t_{d(on)}$	V_{GS}=10V,V_{DD}=30V, I_D=1.5A,R_{GEN}=1Ω		6		ns
Turn-on rise time	t_r			15		ns
Turn-off delay time	$t_{d(off)}$			15		ns
Turn-off fall time	t_f			10		ns
Total Gate Charge	Q_g	V_{DS} =30V,V_{GS} =4.5V,I_D =3A		6		nC
Gate-Source Charge	Q_{gs}			1		nC
Gate-Drain Charge	Q_{gd}			1.3		nC

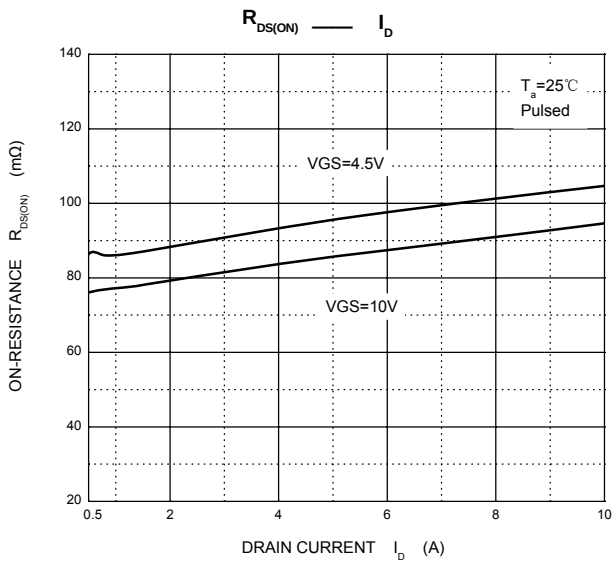
Notes :

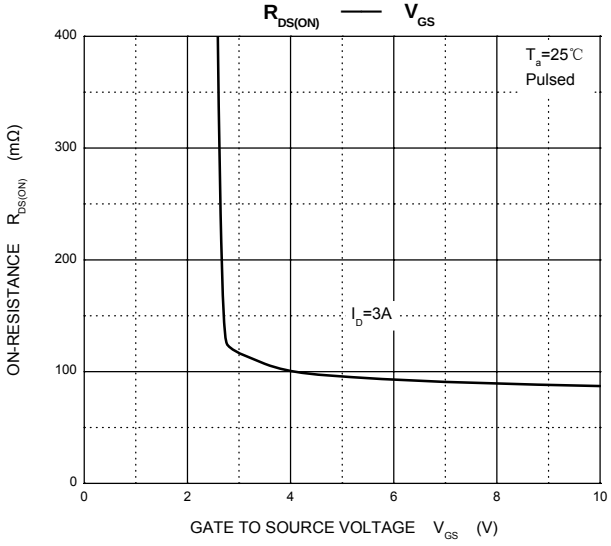
1. Repetitive rating : Pulse width limited by junction temperature.
2. Surface mounted on FR4 board , t≤10s.
3. Pulse Test : Pulse Width≤300μs, Duty Cycle≤0.5%.
4. Guaranteed by design, not subject to producting.

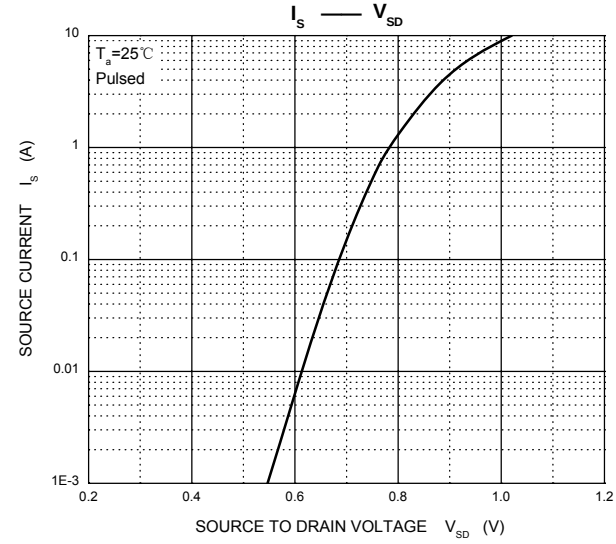
Typical Characteristics

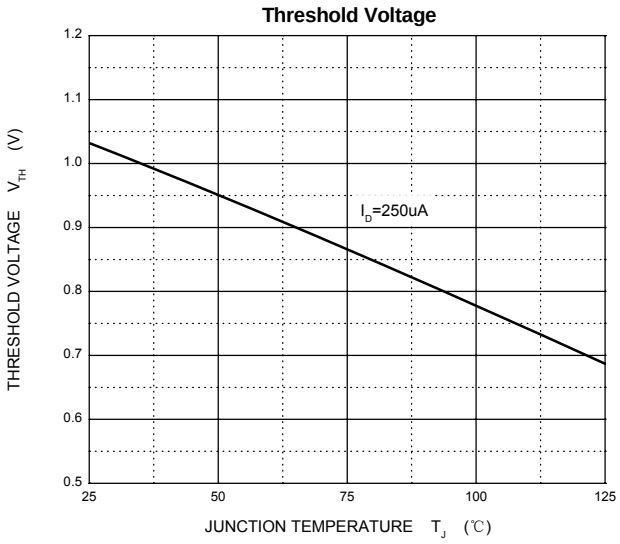




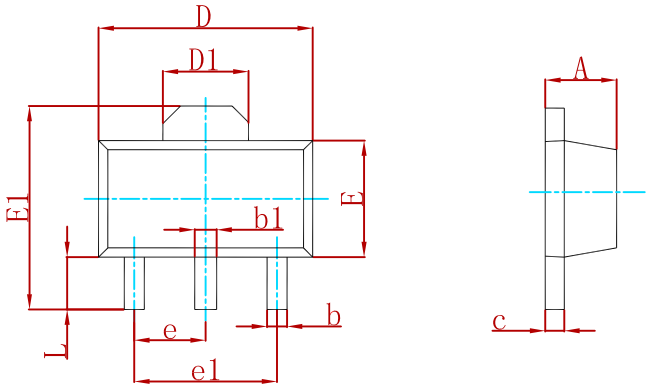






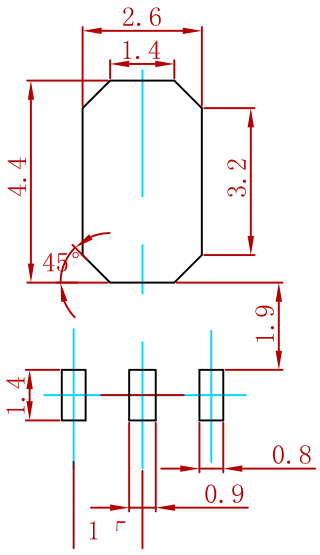


PACKAGE MECHANICAL DATA



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.400	1.600	0.055	0.063
b	0.320	0.520	0.013	0.020
b1	0.400	0.580	0.016	0.023
c	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.550 REF.		0.061 REF.	
E	2.300	2.600	0.091	0.102
E1	3.940	4.250	0.155	0.167
e	1.500 TYP.		0.060 TYP.	
e1	3.000 TYP.		0.118 TYP.	
L	0.900	1.200	0.035	0.047

Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:±0.05mm.
3.The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
3N06-MS	SOT-89	1000

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